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LED420-66-60-110

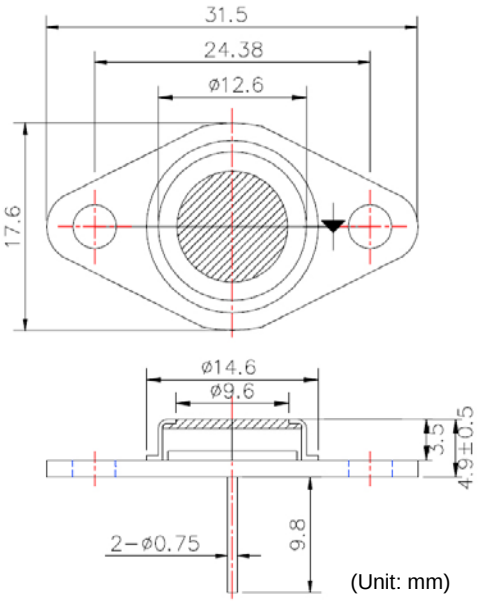
TECHNICAL DATA

High Power LED Array, 60 chips, Glass Window

LED420-66-60-110 is a wide viewing and extremely high output power illuminator assembled with a total of 60 high efficiency InGaN diode chips, mounted on a metal stem TO-66 and covered with a flat glass cap.
These devices are designed for high current operation with proper heat sinking to improver thermal conductive efficiency.

Specifications

- Structure: InGaN, 60 LED chips
- Peak Wavelength: typ. 420 nm
- Optical Output Power: typ. 550 mW
- Package: TO-66 stem,
  Flat glass cap



Absolute Maximum Ratings (T_C=25°C)

Item	Symbol	Value	Unit
Power Dissipation	P_D	12.0	W
Forward Current	I_F	600	mA
Reverse Voltage	V_R	30	V
Operating Temperature	T_{opr}	-30 … +80	°C
Storage Temperature	T_{stg}	-30 … +100	°C
Soldering Temperature *	T_{sol}	265	°C

* must be completed within 3 seconds

Electro-Optical Characteristics

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Total Radiated Power	P_O	I_F = 400 mA	-	550	-	mW
Birghtness	I_V	I_F = 400 mA	-	-	-	mcd
Forward Voltage	V_F	I_F = 400 mA	-	18.0	-	V
Peak Wavelength	λ_P	I_F = 240 mA	-	420	-	nm
Half Width	$\Delta\lambda$	I_F = 240 mA	-	15	-	nm
Viewing Half Angle	$\Theta_{1/2}$	I_F = 240 mA	-	±55	-	deg.

Heat Sink is required, LED has to be keep less than 60°C
Total Radiated Power is measured S3584-08

Notes

- This high power LED must be cooled!
- Do not view directly into the emitting area of the LED during operation!
- The above specifications are for reference purpose only and subjected to change without prior notice.